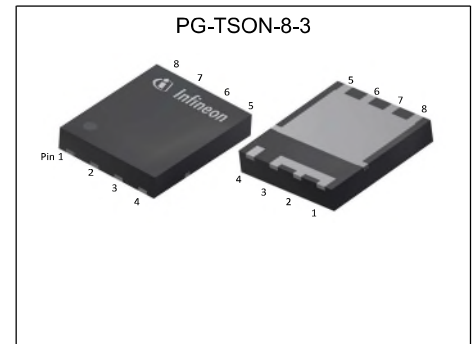


MOSFET

OptiMOS™ 5 Power-Transistor, 80 V

Features

- Optimized for synchronous rectification in server and desktop
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- 175°C rated
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

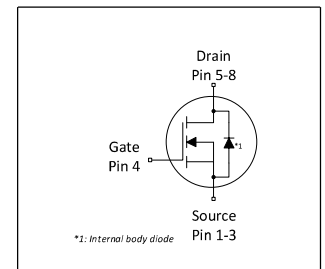


Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	80	V
$R_{DS(on),max}$	2.1	m Ω
I_D	226	A
Q_{oss}	110	nC
$Q_G(0V..10V)$	94	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
BSC021N08NS5	PG-TSON-8-3	021N08N	-

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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	226 160 27	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{K/W}^2)$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	904	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	679	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	214 3.0	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ K/W}^2)$
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.4	0.7	K/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	K/W	-
Device on PCB, 6 cm ² cooling area ²⁾	R_{thJA}	-	-	50	K/W	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	80	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.2	3	3.8	V	$V_{DS}=V_{GS}$, $I_D=146\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=80\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=80\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.6 2.2	2.1 2.9	$\text{m}\Omega$	$V_{GS}=10\text{ V}$, $I_D=50\text{ A}$ $V_{GS}=6\text{ V}$, $I_D=25\text{ A}$
Gate resistance ¹⁾	R_G	-	1.9	2.9	Ω	-
Transconductance	g_{fs}	70	140	-	S	$ V_{DS} >2 I_D /R_{DS(on)max}$, $I_D=50\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	6600	8600	pF	$V_{GS}=0\text{ V}$, $V_{DS}=40\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	1100	1400	pF	$V_{GS}=0\text{ V}$, $V_{DS}=40\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{riss}	-	47	82	pF	$V_{GS}=0\text{ V}$, $V_{DS}=40\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	13	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Rise time	t_r	-	17	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	44	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Fall time	t_f	-	20	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=3\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	29	-	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	20	-	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ¹⁾	Q_{gd}	-	20	29	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	29	-	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ¹⁾	Q_g	-	94	117	nC	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.4	-	V	$V_{DD}=40\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	81	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	110	147	nC	$V_{DD}=40\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test.

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	159	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	904	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.83	1.1	V	$V_{GS}=0\text{ V}, I_F=50\text{ A}, T_j=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	50	100	ns	$V_R=40\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	80	160	nC	$V_R=40\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$

¹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

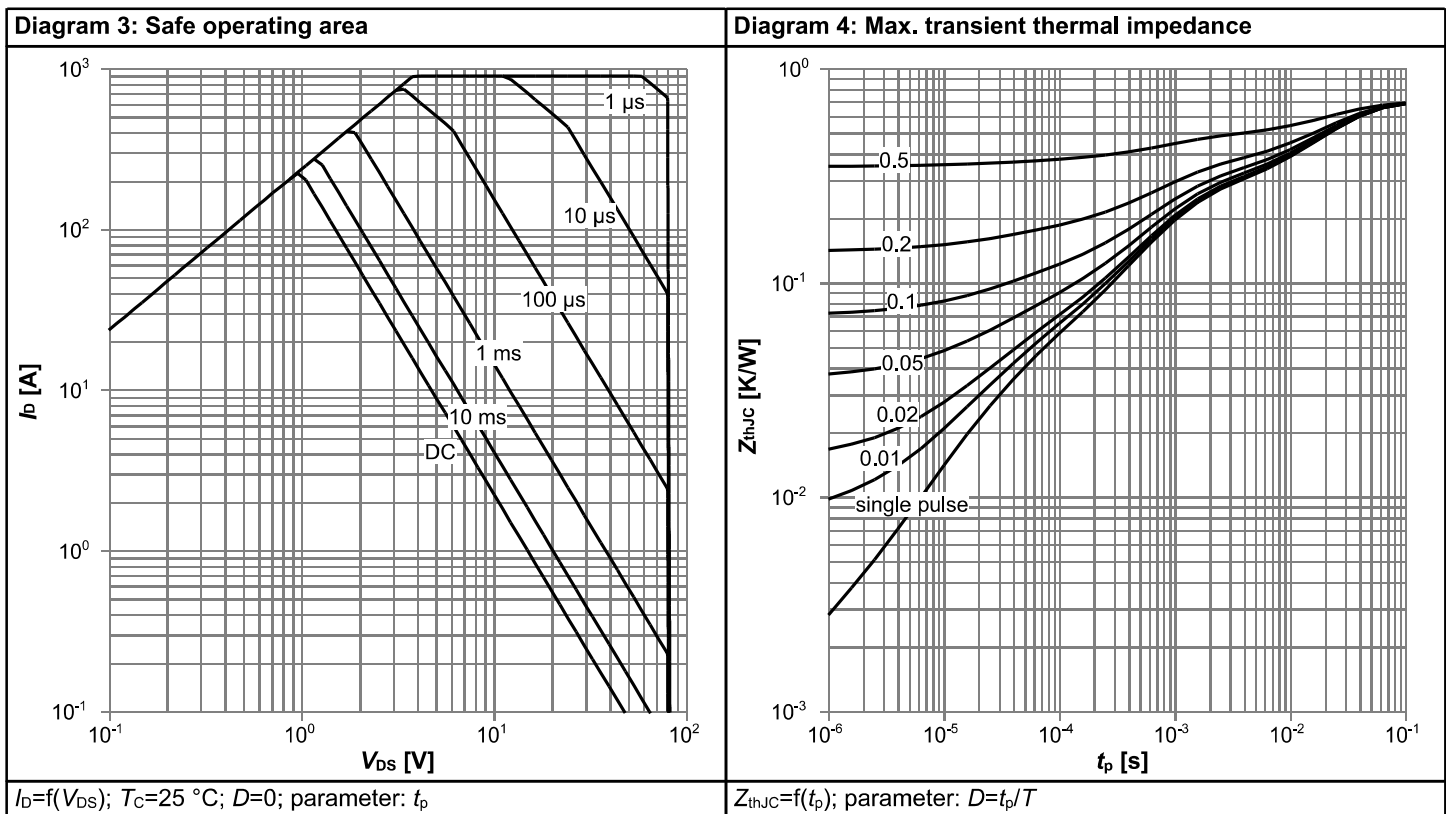
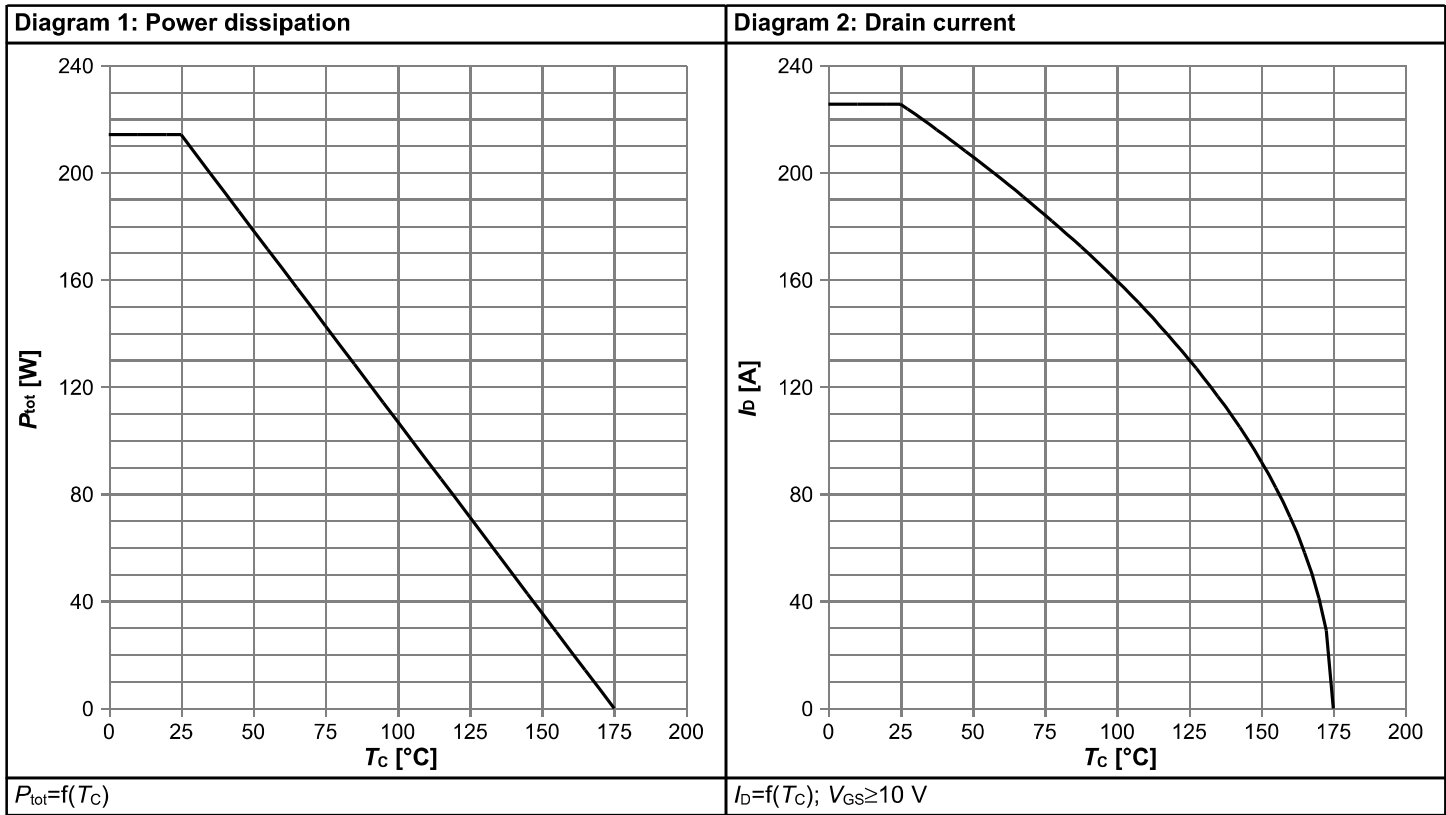
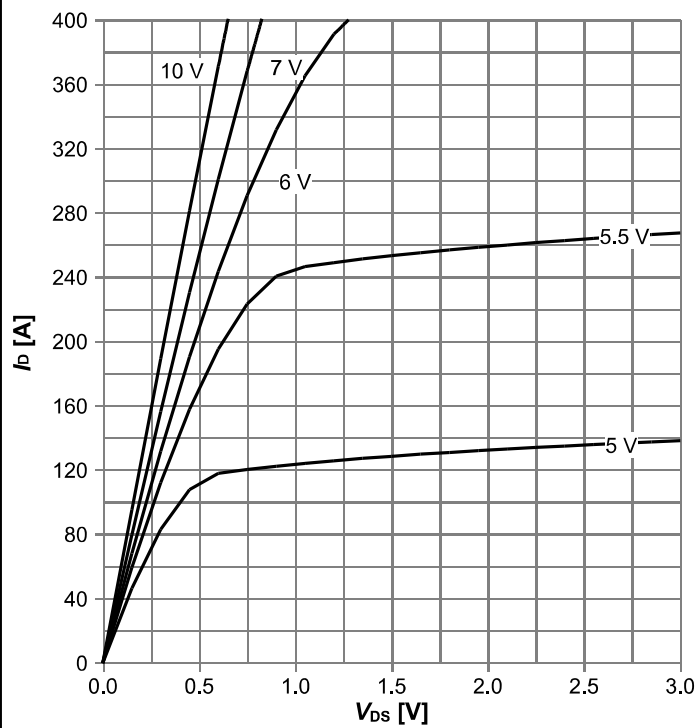
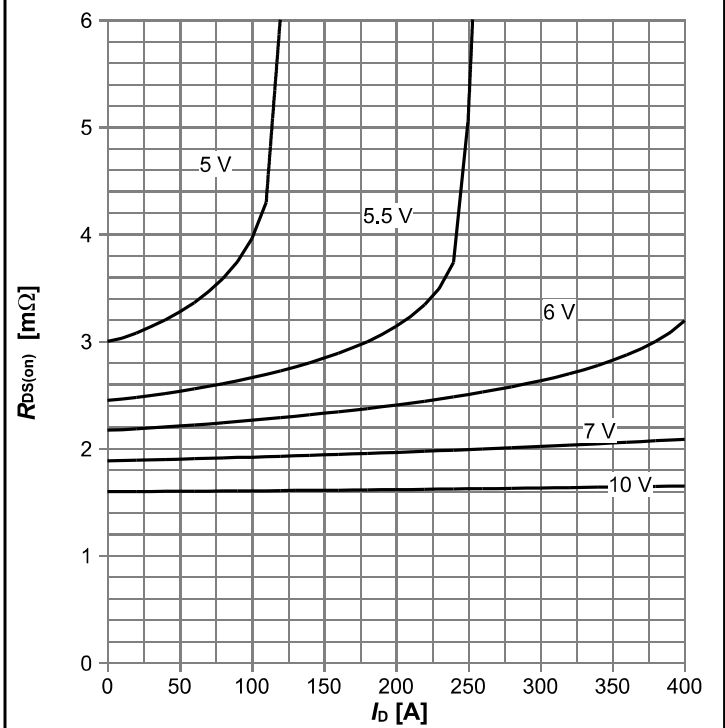


Diagram 5: Typ. output characteristics



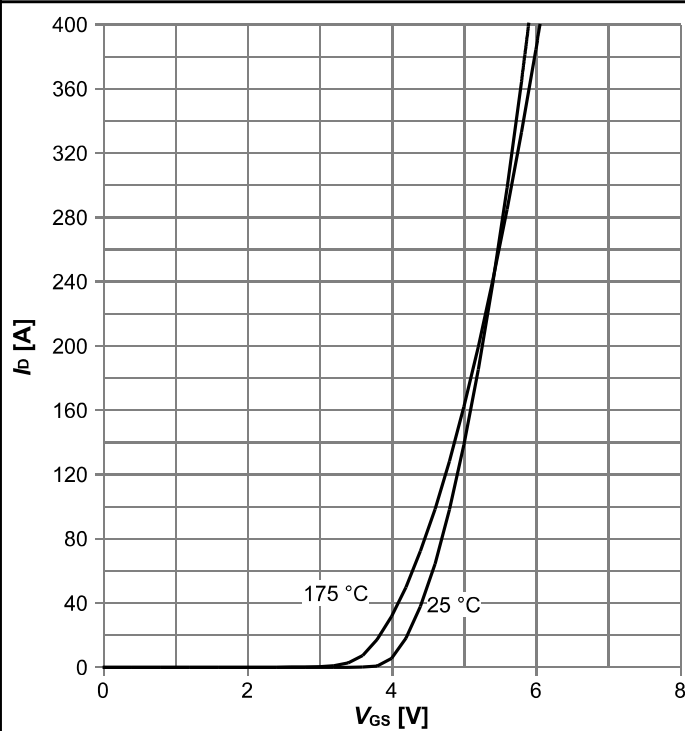
$I_D = f(V_{DS})$; $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



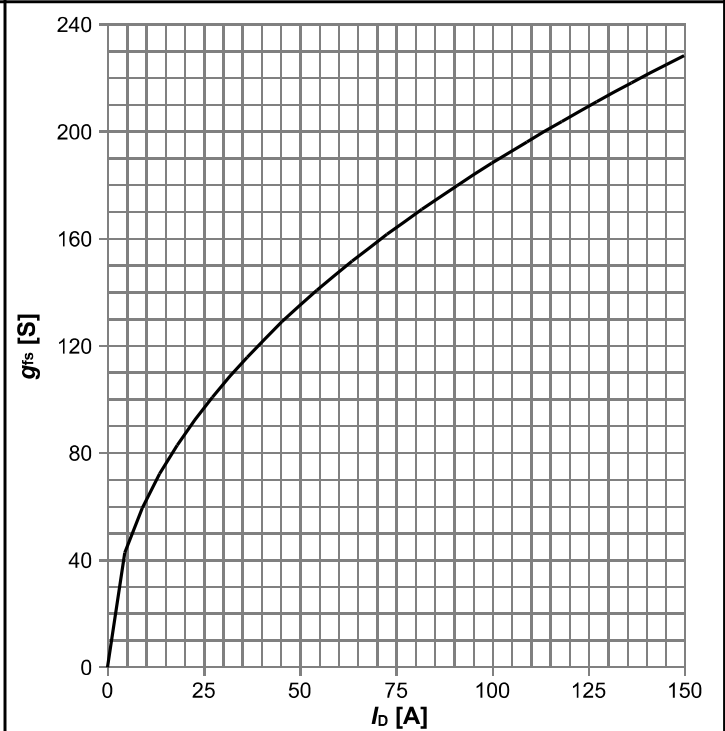
$R_{DS(on)} = f(I_D)$; $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



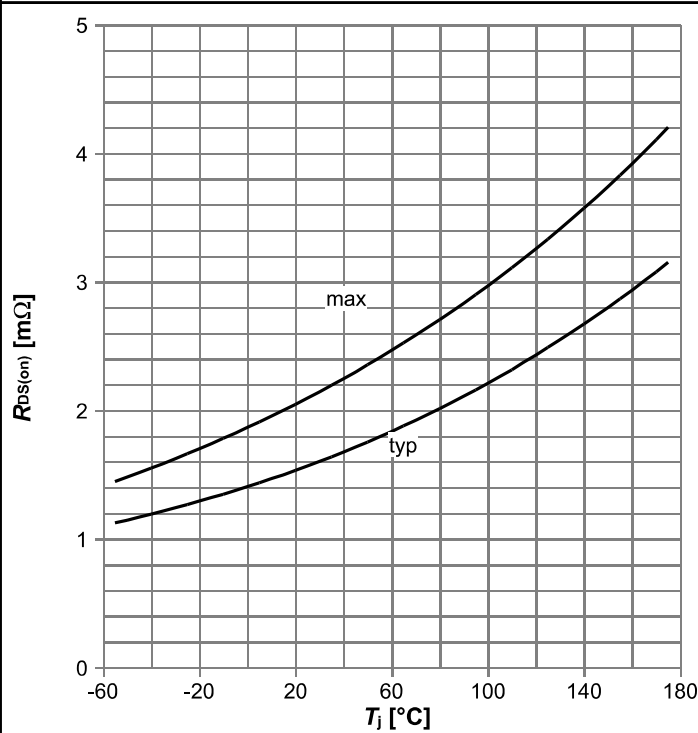
$I_D = f(V_{GS})$; $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



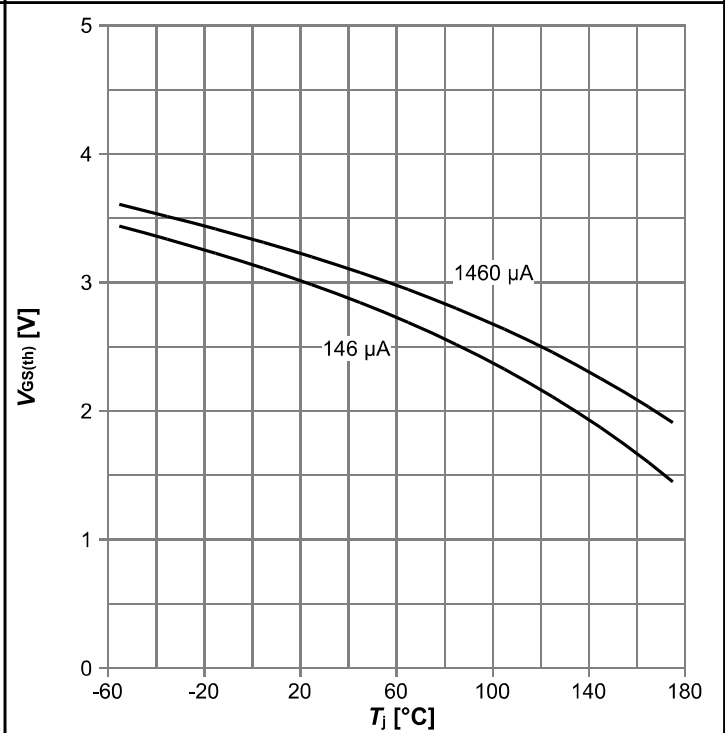
$g_{fs} = f(I_D)$, $V_{DS} = 3\text{ V}$, $T_j = 25\text{ °C}$

Diagram 9: Drain-source on-state resistance



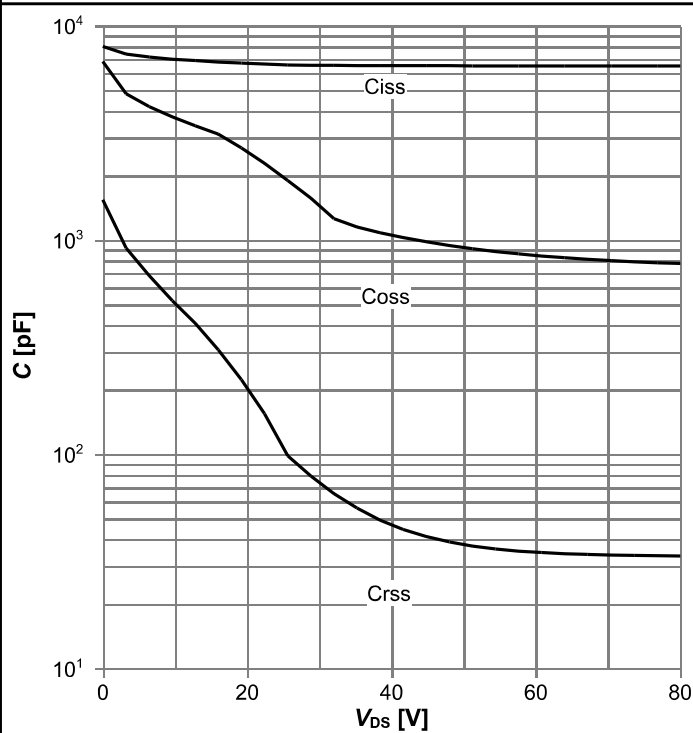
$R_{DS(on)}=f(T_j)$; $I_D=50$ A; $V_{GS}=10$ V

Diagram 10: Typ. gate threshold voltage



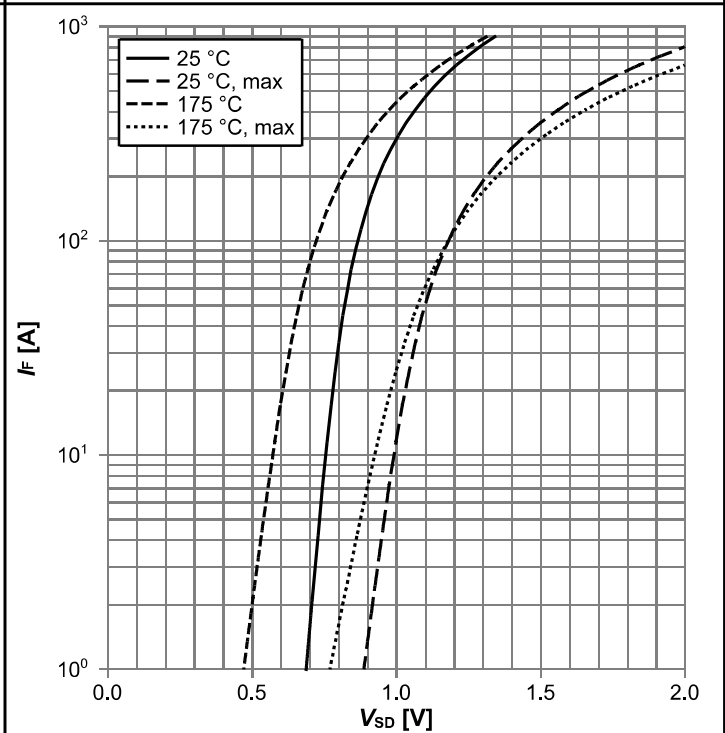
$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$

Diagram 11: Typ. capacitances



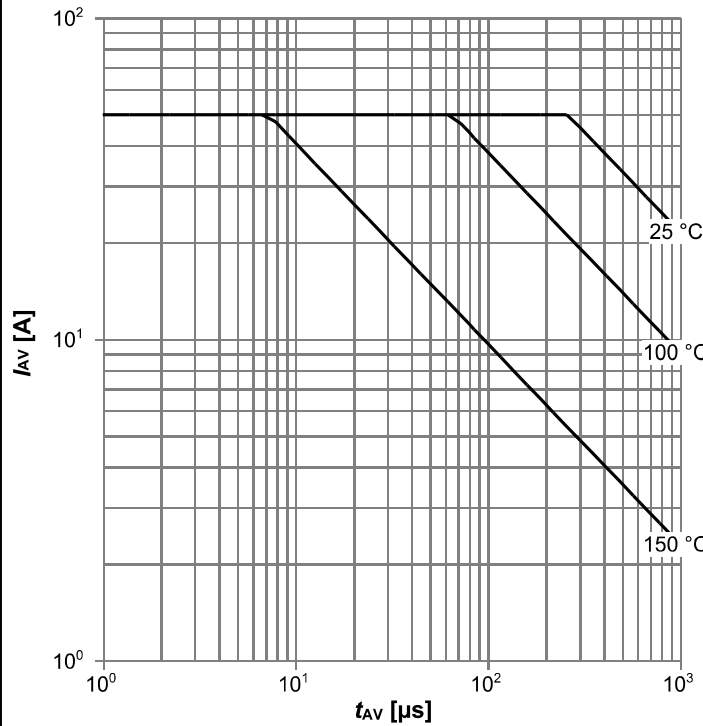
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz

Diagram 12: Forward characteristics of reverse diode



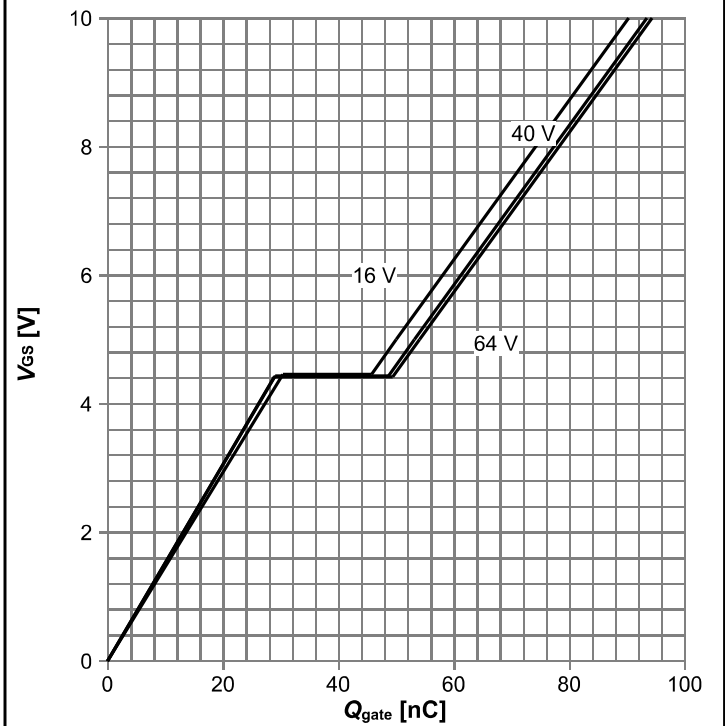
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



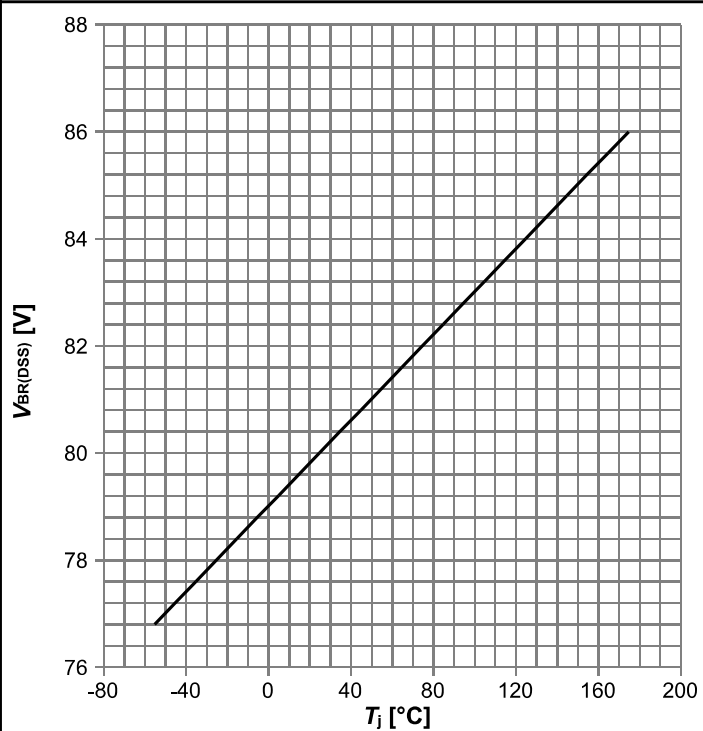
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega; \text{parameter: } T_{j(\text{start})}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{\text{gate}}), I_D=50 \text{ A pulsed}, T_j=25 \text{ °C}; \text{parameter: } V_{DD}$

Diagram 15: Drain-source breakdown voltage

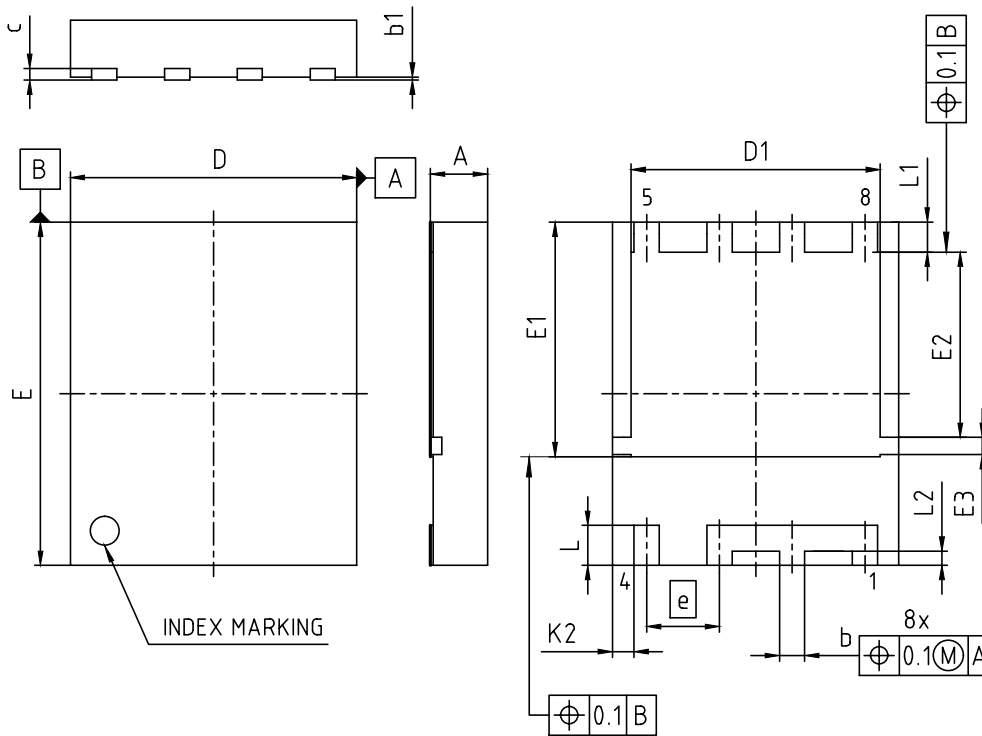


$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Diagram Gate charge waveforms



5 Package Outlines



DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	-	1.10
b	0.34	0.54
b1	-	0.05
c	0.20	
D	4.90	5.10
D1	4.25	4.45
E	5.90	6.10
E1	4.00	4.20
E2	3.14	3.34
E3	0.20	0.40
e	1.27	
K2	(0.37)	
L	0.60	0.80
L1	0.43	0.63
L2	(0.25)	

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Figure 1 Outline PG-TSON-8-3, dimensions in mm/inches

Revision History

BSC021N08NS5

Revision: 2021-03-17, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2018-03-19	Release of final version
2.1	2021-03-17	Update current rating

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